

6/m6,394

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	10204	ferroelectric near3 memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:17
2	BRS	L2	538258	plug	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:17
3	BRS	L3	13182	oxygen near3 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:18
4	BRS	L4	83553	lower near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:19
5	BRS	L5	81364	upper near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:19
6	BRS	L6	43326	ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:19
7	BRS	L7	389	2 same 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:19
8	BRS	L8	44933	4 same 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:20
9	BRS	L9	158	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:20
10	BRS	L10	163606	"438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:20
11	BRS	L11	297654	"257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:20
12	BRS	L12	126	9 and (10 or 11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:41
13	BRS	L13	2133	438/239	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:46
14	BRS	L14	4212	438/253	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:46
15	BRS	L15	837	438/393	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	5945	438/396	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:46
17	BRS	L17	260	3 and 16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:46
18	BRS	L18	113	5 and 17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:47
19	BRS	L19	69	18 not 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:51
20	BRS	L20	2429	5 and (13 or 14 or 15 or 16)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:51
21	BRS	L21	344	3 and (13 or 14 or 15 or 16)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:51
22	BRS	L22	290	21 not 12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 15:52
23	BRS	L23	221	22 not 19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:08
24	BRS	L24	0	"1020000002986 0"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:10
25	BRS	L25	0	2000-0029860	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:10
26	BRS	L26	7	semiconductor and large and scale and oxide and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:11
27	BRS	L27	18912	semiconductor and large and scale and oxide and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:11
28	BRS	L29	2	28 and hiratani	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:11

	Type	L #	Hits	Search Text	DBs	Time Stamp
29	BRS	L28	19	27 and fujisaki	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:13
30	BRS	L30	32204	oxygen and deficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:14
31	BRS	L31	0	28 and 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:14
32	BRS	L32	523	27 and 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:14
33	BRS	L33	324	32 and crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:14
34	BRS	L34	224	33 and upper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:14
35	BRS	L35	14	34 and hitachi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:17
36	BRS	L36	82	samsung and jung and kim and lee and nam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:17
37	BRS	L37	11	36 and ferroelectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:21
38	BRS	L38	8	hitachi and fujisaki and hiratani and miki	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:39
39	BRS	L39	57	"5119154"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:45
40	BRS	L40	43	"5854104"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/03/03 16:45